Dual 4-Input Multiplexer with 3-State Outputs

The MC74AC253/74ACT253 is a dual 4–input multiplexer with 3–state outputs. It can select two bits of data from four sources using common select inputs. The outputs may be individually switched to a high impedance state with a HIGH on the respective Output Enable (\overline{OE}) inputs, allowing the outputs to interface directly with bus oriented systems.

- Multifunctional Capability
- Noninverting 3–State Outputs
- Outputs Source/Sink 24 mA
- 'ACT253 Has TTL Compatible Inputs
- These are Pb-Free Devices

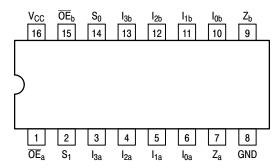


Figure 1. Pinout: 16-Lead Packages Conductors (Top View)

PIN NAME

PIN	FUNCTION
I _{0a} –I _{3a}	Side A Data Inputs
I _{0b} –I _{3b}	Side B Data Inputs
S ₀ , S ₁	Common Select Inputs
ŌĒa	Side A Output Enable Input
ŌE _b	Side B Output Enable Input
$Z_{a,}Z_{b}$	3-State Outputs



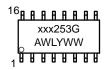
ON Semiconductor™

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MARKING DIAGRAMS



SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



xxx = AC or ACT

A = Assembly Location

WL or L = Wafer Lot Y = Year WW or W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

TRUTH TABLE

Sel Inp			Data I	nputs		Output Enable	Outputs
S ₀	S ₁	I ₀	I ₁	l ₂	l ₃	ŌĒ	Z
Х	Χ	Χ	Χ	Χ	Χ	Н	Z
L	L	L	Х	X	X	L	L
L	L	Н	Х	Χ	Χ	L	Н
Н	L	Χ	L	X	Х	L	L
Н	L	X	Н	Χ	Χ	L	Н
L	Н	X	X	L	Χ	L	L
L	Н	Χ	Χ	Н	Х	L	Н
Н	Н	Χ	Χ	X	L	L	L
Н	Н	Χ	Χ	Χ	Н	L	Н

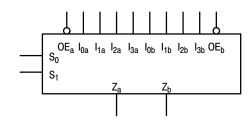


Figure 2. Logic Symbol

Address inputs S_0 and S_1 are common to both sections.

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

Z = High Impedance

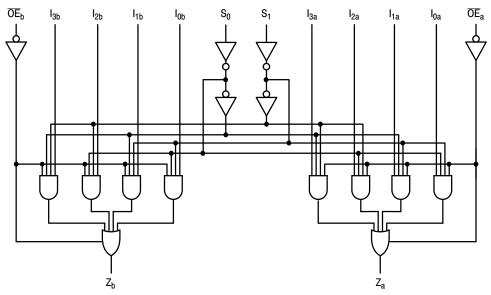
FUNCTIONAL DESCRIPTION

The MC74AC253/74ACT253 contains two identical 4–input multiplexers with 3–state outputs. They select two bits from four sources selected by common Select inputs (S_0 , S_1). The 4–input multiplexers have individual Output Enable (\overline{OE}_a , \overline{OE}_b) inputs which, when HIGH, force the outputs to a high impedance (High Z) state. This device is the logic implementation of a 2–pole, 4–position switch, where the position of the switch is determined by the logic levels

supplied to the two select inputs. The logic equations for the outputs are shown:

$$\begin{split} Z_{a} &= \overline{OE}_{a^{\bullet}}(I_{0a^{\bullet}}\overline{S}_{1^{\bullet}}\overline{S}_{0^{+}}I_{1a^{\bullet}}\overline{S}_{1^{\bullet}}S_{0^{+}}\\ I_{2a^{\bullet}}S_{1^{\bullet}}\overline{S}_{0^{+}}I_{3a^{\bullet}}S_{1^{\bullet}}S_{0})\\ Z_{b} &= \overline{OE}_{b^{\bullet}}(I_{0b^{\bullet}}\overline{S}_{1^{\bullet}}\overline{S}_{0^{+}}I_{1b^{\bullet}}\overline{S}_{1^{\bullet}}S_{0^{+}}\\ I_{2b^{\bullet}}S_{1^{\bullet}}\overline{S}_{0^{+}}I_{3b^{\bullet}}S_{1^{\bullet}}S_{0}) \end{split}$$

If the outputs of 3–state devices are tied together, all but one device must be in the high impedance state to avoid high currents that would exceed the maximum ratings. Designers should ensure that Output Enable signals to 3–state devices whose outputs are tied together are designed so that there is no overlap.



NOTE: This diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Figure 3. Logic Diagram

MAXIMUM RATINGS

Parameter		Value	Unit
DC Supply Voltage		-0.5 to +7.0	V
DC Input Voltage		$-0.5 \le V_{CC} + 0.5$	V
DC Output Voltage (Note 1)		$-0.5 \le V_{CC} + 0.5$	V
DC Input Diode Current	±20	mA	
DC Output Diode Current	±50	mA	
DC Output Sink/Source Current		±50	mA
DC Supply Current per Output Pin		±50	mA
DC Ground Current per Output Pin		±50	mA
Storage Temperature Range	-65 to +150	°C	
Lead temperature, 1 mm from Case for 10 Seconds	260	°C	
Junction temperature under Bias		+150	°C
Thermal Resistance (Note 2)	SOIC TSSOP	69.1 103.8	°C/W
Power Dissipation in Still Air at 65°C (Note 3)	SOIC TSSOP	500 500	mW
Moisture Sensitivity		Level 1	
Flammability Rating Oxygen	UL 94 V-0 @ 0.125 in		
Machi	> 2000 > 200 > 1000	V	
Latch-Up Performance Above V _{CC} and Below GNI	±100	mA	
	DC Supply Voltage DC Input Voltage DC Output Voltage (Note 1) DC Input Diode Current DC Output Diode Current DC Output Sink/Source Current DC Supply Current per Output Pin DC Ground Current per Output Pin Storage Temperature Range Lead temperature, 1 mm from Case for 10 Seconds Junction temperature under Bias Thermal Resistance (Note 2) Power Dissipation in Still Air at 65°C (Note 3) Moisture Sensitivity Flammability Rating Oxygen ESD Withstand Voltage Human Book Maching Charged Devi	DC Supply Voltage DC Input Voltage DC Output Voltage (Note 1) DC Input Diode Current DC Output Diode Current DC Output Sink/Source Current DC Supply Current per Output Pin DC Ground Current per Output Pin Storage Temperature Range Lead temperature, 1 mm from Case for 10 Seconds Junction temperature under Bias Thermal Resistance (Note 2) SOIC TSSOP Power Dissipation in Still Air at 65°C (Note 3) SOIC TSSOP Moisture Sensitivity Flammability Rating Oxygen Index: 30% – 35% ESD Withstand Voltage Human Body Model (Note 4) Machine Model (Note 5) Charged Device Model (Note 6) Latch-Up Performance Above V _{CC} and Below GND at 85°C (Note 7)	DC Supply Voltage $-0.5 \text{ to } +7.0$ DC Input Voltage $-0.5 \leq V_{CC} + 0.5$ DC Output Voltage (Note 1) $-0.5 \leq V_{CC} + 0.5$ DC Input Diode Current ± 20 DC Output Diode Current ± 50 DC Output Sink/Source Current ± 50 DC Supply Current per Output Pin ± 50 DC Ground Current per Output Pin ± 50 Storage Temperature Range $-65 \text{ to } +150$ Lead temperature, 1 mm from Case for 10 Seconds 260 Junction temperature under Bias $+150$ Thermal Resistance (Note 2) $-65 \text{ to } +150$ Thermal Resistance (Note 2) $-69.1 \\ TSSOP$ Moisture Sensitivity $-69.1 \\ TSSOP$ ESD Withstand Voltage $-69.1 \\ TSSOP$ Human Body Model (Note 4) $-69.1 \\ TSSOP$ Model (Note 5) $-600 \\ TSSOP$ Machine Model (Note 4) $-69.1 \\ TSSOP$ Machine Model (Note 5) $-200 \\ -200 \\ -200 \\ -200 \\ -1000$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Io absolute maximum rating must be observed.
- 2. The package thermal impedance is calculated in accordance with JESD51-7.
- 3. 500 mW at 65°C; derate to 300 mW by 10 mW/ from 65°C to 85°C.
- 4. Tested to EIA/JESD22-A114-A.
- 5. Tested to EIA/JESD22-A115-A.
- 6. Tested to JESD22-C101-A.
- 7. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit				
V	Control o Vella ma	'AC	2.0	5.0	6.0					
V _{CC}	Supply Voltage	'ACT	4.5	5.0	5.5	V				
V _{IN} , V _{OUT}	DC Input Voltage, Output Voltage (Ref. to GND)		0	-	V _{CC}	V				
		V _{CC} @ 3.0 V	-	150	_					
t _r , t _f	Input Rise and Fall Time (Note 1) 'AC Devices except Schmitt Inputs	V _{CC} @ 4.5 V	-	40	_	ns/V				
	The Bornood oxeopt Commit inpute	V _{CC} @ 5.5 V	-	25	_					
	Input Rise and Fall Time (Note 2)	V _{CC} @ 4.5 V	-	10	_	- A /				
t _r , t _f	'ACT Devices except Schmitt Inputs	-	8.0	_	ns/V					
T _A	Operating Ambient Temperature Range	-40	25	85	°C					
I _{OH}	Output Current – High	-	-	-24	mA					
I _{OL}	Output Current – Low	-	_	24	mA					

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

- V_{IN} from 30% to 70% V_{CC}; see individual Data Sheets for devices that differ from the typical input rise and fall times.
 V_{IN} from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

DC CHARACTERISTICS

			74	AC	74AC			
Symbol	Parameter	V _{CC} (V)	T _A = +25°C		T _A = -40°C to +85°C	Unit	Conditions	
			Тур	Guar	anteed Limits			
V _{IH}	Minimum High Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	2.1 3.15 3.85	2.1 3.15 3.85	V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V	
V _{IL}	Maximum Low Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	0.9 1.35 1.65	0.9 1.35 1.65	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V	
V _{OH}	Minimum High Level Output Voltage	3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	V	I _{OUT} = -50 μA	
		3.0 4.5 5.5	- - -	2.56 3.86 4.86	2.46 3.76 4.76	V	*V _{IN} = V _{IL} or V _{IH} -12 mA I _{OH} -24 mA -24 mA	
V _{OL}	Maximum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	٧	Ι _{ΟυΤ} = 50 μΑ	
		3.0 4.5 5.5	- - -	0.36 0.36 0.36	0.44 0.44 0.44	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ 12 mA I_{OL} 24 mA 24 mA	
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	$V_I = V_{CC}$, GND	
I _{OZ}	Maximum 3-State Current	5.5	-	±0.5	±5.0	μΑ	V_{I} (OE) = V_{IL} , V_{IH} V_{I} = V_{CC} , GND V_{O} = V_{CC} , GND	
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max	
I _{OHD}	Output Current	5.5	-	_	- 75	mA	V _{OHD} = 3.85 V Min	
Icc	Maximum Quiescent Supply Current	5.5	-	8.0	80	μΑ	V _{IN} = V _{CC} or GND	

^{*}All outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time.

NOTE: I_{IN} and I_{CC} @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V V_{CC} .

AC CHARACTERISTICS (For Figures and Waveforms – See Section 3 of the ON Semiconductor FACT Data Book, DL138/D)

				74AC		74AC			
Symbol	Parameter	V _{CC} * (V)	T _A = +25°C C _L = 50 pF			T _A = -40°C to +85°C C _L = 50 pF		Unit	Fig. No.
			Min	Тур	Max	Min	Max		
t _{PLH}	Propagation Delay S _n to Z _n	3.3 5.0	2.0 2.0		15.5 11.0	2.0 1.5	17.5 12.5	ns	3–6
t _{PHL}	Propagation Delay S _n to Z _n	3.3 5.0	2.5 2.0	-	16.0 11.5	2.0 1.5	18.0 13.0	ns	3–6
t _{PLH}	Propagation Delay I_n to Z_n	3.3 5.0	1.5 1.5	-	14.5 10.0	1.5 1.5	17.0 11.5	ns	3–5
t _{PHL}	Propagation Delay I_n to Z_n	3.3 5.0	2.0 1.5		13.0 9.5	1.5 1.5	15.0 11.0	ns	3–5
t _{PZH}	Output Enable Time	3.3 5.0	1.5 1.5	-	8.0 6.0	1.0 1.0	8.5 6.5	ns	3–7
t _{PZL}	Output Enable Time	3.3 5.0	1.5 1.5	-	8.0 6.0	1.0 1.0	9.0 7.0	ns	3–8
t _{PHZ}	Output Disable Time	3.3 5.0	2.0 2.0		9.5 8.0	1.5 1.5	10.0 8.5	ns	3–7
t _{PLZ}	Output Disable Time	3.3 5.0	1.5 1.5	_ _	8.0 7.0	1.0 1.0	9.0 7.5	ns	3–8

^{*}Voltage Range 3.3 V is 3.3 V ± 0.3 V. *Voltage Range 5.0 V is 5.0 V ± 0.5 V.

DC CHARACTERISTICS

			74 <i>A</i>	CT	74ACT		
Symbol	Parameter	V _{CC} (V)	T _A = +25°C		T _A = -40°C to +85°C	Unit	Conditions
			Тур	Guar	anteed Limits		
V _{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I _{OUT} = -50 μA
		4.5 5.5	- -	3.86 4.86	3.76 4.76	V	* V _{IN} = V _{IL} or V _{IH} -24 mA I OH -24 mA
V _{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V	I _{OUT} = 50 μA
		4.5 5.5		0.36 0.36	0.44 0.44	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ $^{24} \text{ mA}$ $^{1}_{OL}$ $^{24} \text{ mA}$
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	V _I = V _{CC} , GND
ΔI_{CCT}	Additional Max. I _{CC} /Input	5.5	0.6	_	1.5	mA	$V_{I} = V_{CC} - 2.1 \text{ V}$
l _{OZ}	Maximum 3-State Current	5.5	-	±0.5	±5.0	μА	V_{I} (OE) = V_{IL} , V_{IH} V_{I} = V_{CC} , GND V_{O} = V_{CC} , GND
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}	Output Current	5.5	-	-	-75	mA	V _{OHD} = 3.85 V Min
I _{CC}	Maximum Quiescent Supply Current	5.5	-	8.0	80	μА	V _{IN} = V _{CC} or GND

 $^{^\}star All$ outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time.

AC CHARACTERISTICS (For Figures and Waveforms - See Section 3 of the ON Semiconductor FACT Data Book, DL138/D)

				74ACT		74ACT			
Symbol	Parameter	V _{CC} * (V)	T _A = +25°C C _L = 50 pF			T _A = -40°C to +85°C C _L = 50 pF		Unit	Fig. No.
			Min	Тур	Max	Min	Max		
t _{PLH}	Propagation Delay S_n to Z_n	5.0	2.0	1	11.5	2.0	13.0	ns	3–6
t _{PHL}	Propagation Delay S_n to Z_n	5.0	3.0	ı	13.0	2.5	14.5	ns	3–6
t _{PLH}	Propagation Delay I_n to Z_n	5.0	2.5	ı	10.0	2.0	11.0	ns	3–5
t _{PHL}	Propagation Delay I_n to Z_n	5.0	3.5	ı	11.0	3.0	12.5	ns	3–5
t _{PZH}	Output Enable Time	5.0	2.0	-	7.5	1.5	8.5	ns	3–7
t _{PZL}	Output Enable Time	5.0	2.0	-	8.0	1.5	9.0	ns	3–8
t _{PHZ}	Output Disable Time	5.0	3.0	-	9.5	2.5	10.0	ns	3–7
t _{PLZ}	Output Disable Time	5.0	2.5	-	7.5	2.0	8.5	ns	3–8

^{*} Voltage Range 5.0 V is 5.0 V ± 0.5 V.

CAPACITANCE

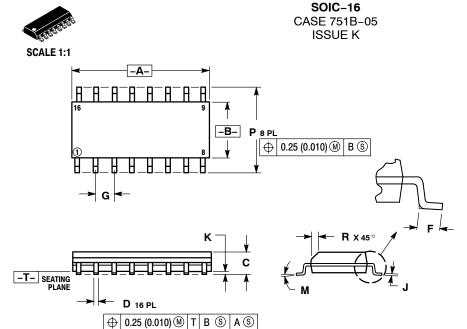
Symbol	Parameter	Value Typ	Unit	Test Conditions
C _{IN}	Input Capacitance	4.5	pF	V _{CC} = 5.0 V
C _{PD}	Power Dissipation Capacitance	50	pF	V _{CC} = 5.0 V

ORDERING INFORMATION

Device Order Number	Package	Shipping [†]
MC74AC253DG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74AC253DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74AC253DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel
MC74ACT253DG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74ACT253DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74ACT253DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	#1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION		BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.		7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	OOL DEDING	COOTDONT
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	FOOTPRINT
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		i.40 — →
								- 0	.40
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				10% 1.12
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPU	Τ\		1	16
3.	DRAIN, #2	3.		3.	COMMON DRAIN (OUTPU			, L .	'0
3. 4.	DRAIN, #2	3. 4.	CATHODE	3. 4.	GATE P-CH	1)		- —	
4. 5.	DRAIN, #2	4. 5.	CATHODE	4. 5.	COMMON DRAIN (OUTPU	Τ\		, , , , , , , , , , , , , , , , , , , 	
5. 6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU		16	5X 1 -	
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU		0.5	58	, L
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	•,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU	T)			
11.	GATE, #3	11.		11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3	12.		12.	COMMON DRAIN (OUTPU				
13.	GATE, #2	13.		13.	GATE N-CH	.,			
14.	SOURCE, #2	14.		14.	COMMON DRAIN (OUTPU	T)			V PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU				1 <u>+=</u> 1_1
16.	SOURCE, #1		ANODE	16.	SOURCE N-CH	.,			
								□ 8	9 + - + -
									~
									' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '
									DIMENSIONS: MILLIMETERS

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